

Supporting Information

Low-threshold nanowire laser based on composition-symmetric semiconductor nanowires

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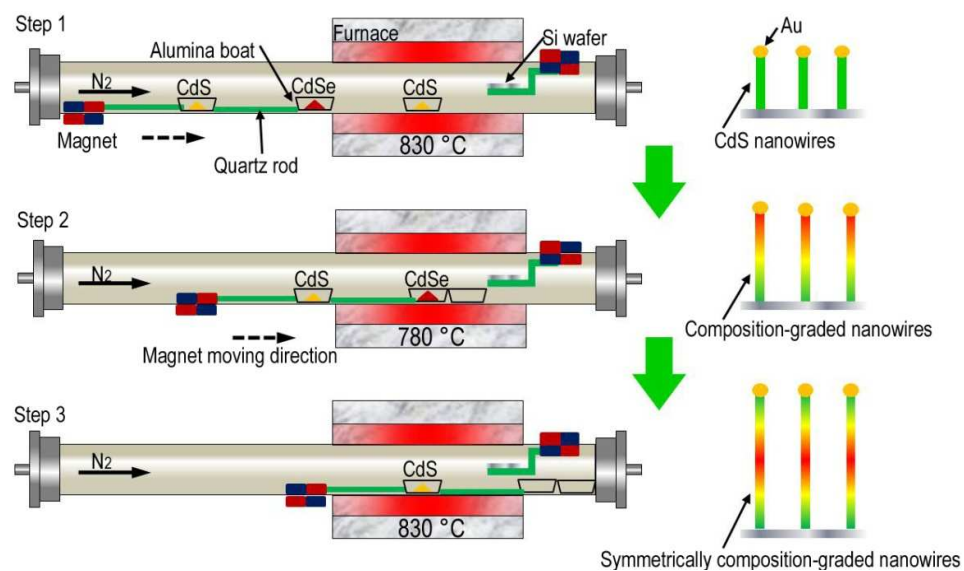


Figure S1. Schematic diagrams of the experimental setup and the growth processes for the symmetrically composition-graded NWs.

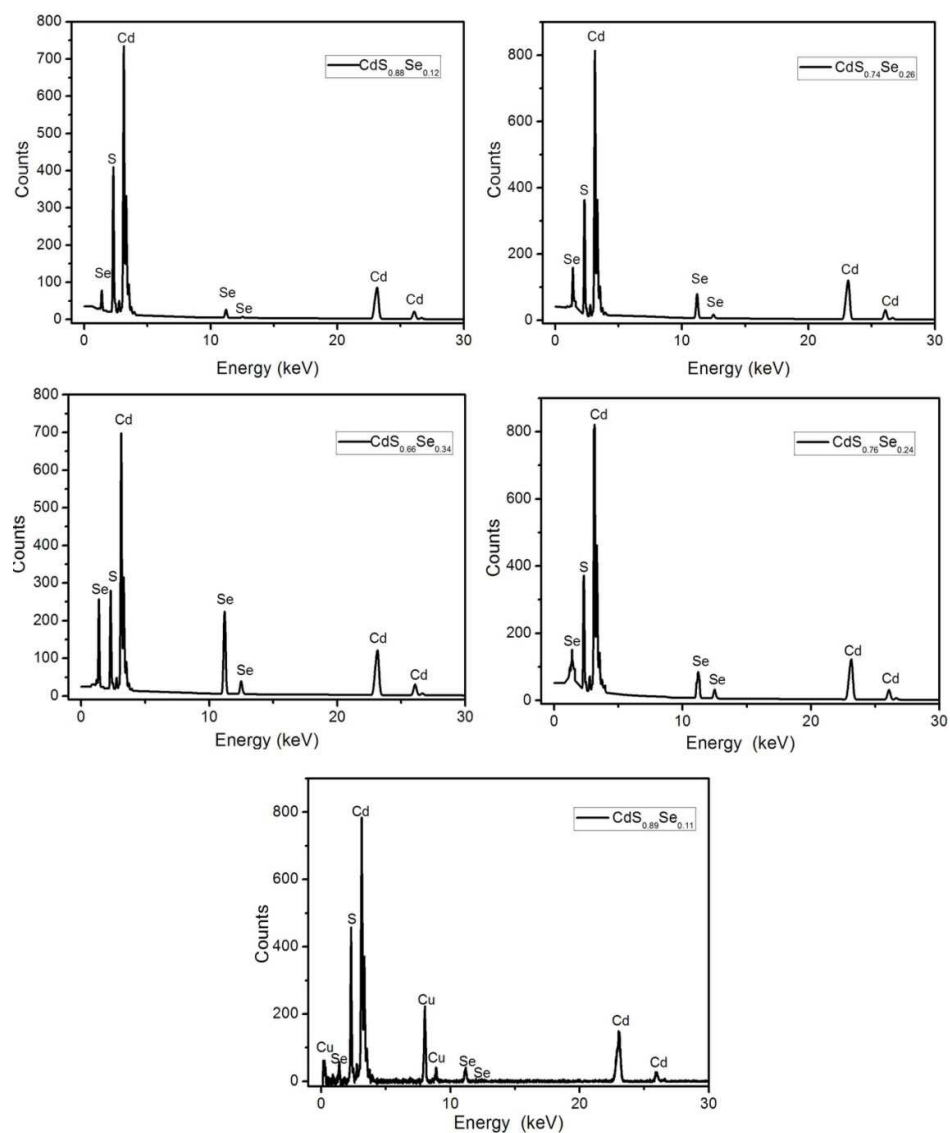


Figure S2. Alloy compositions of the symmetrically composition-graded NWs (given in Figure 2B), collected from the *in situ* TEM-EDS results (Philip Tecnai F20).

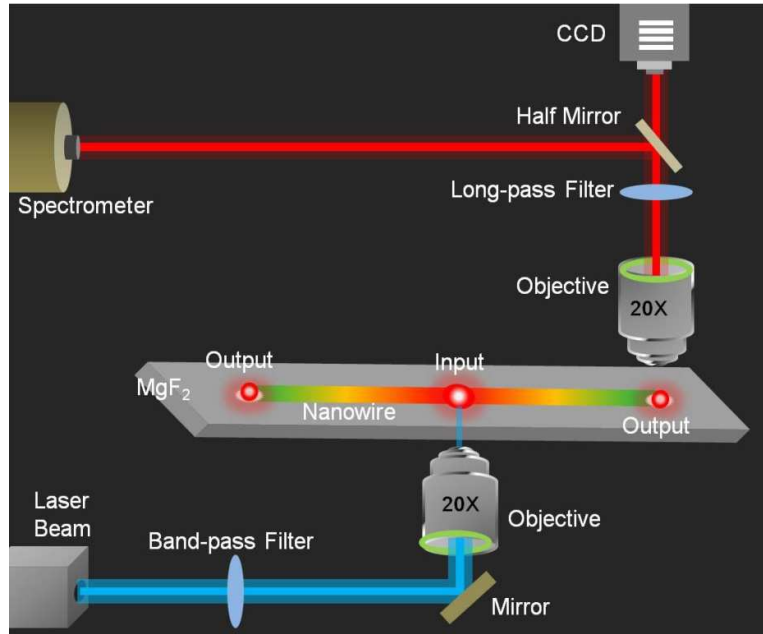


Figure S3. Schematic demonstration of the experimental setup for the optical characterization.

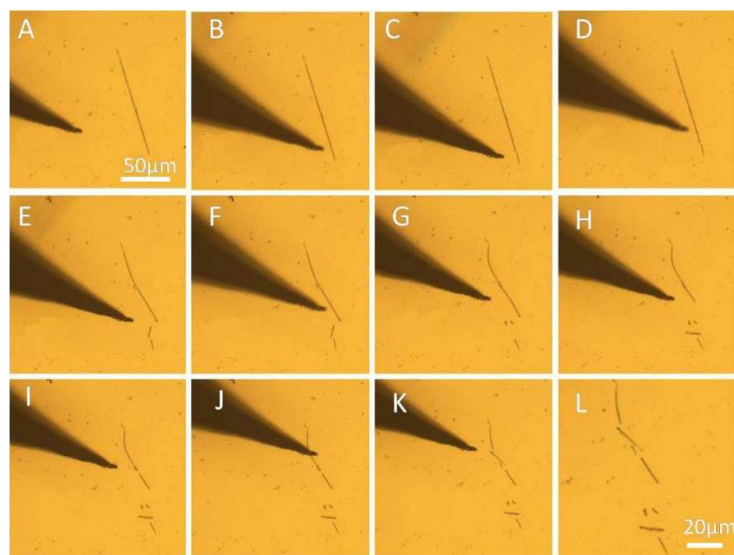


Figure S4. Optical microscope images of cutting NWs by homemade wolfram probe.

The micromanipulation is carried out by a homemade wolfram probe mounted on a precisely controlled 3-dimensional moving stage under an optical microscope equipped with a long-distance objective. The optical images (from A to L) illustrate the whole process.

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